# 5.2 Process Integration

5.2.1 Chips on Wafers

We now have a crude idea of *what* we want to make. The question now is *how* we are going to do it.

- We start with a suitable piece of a **Si** crystal, a **Si wafer**. A wafer is a thin (about **650 μm)** round piece of rather perfect **Si** single crystal with a typical diameter (in the year **2000**) of **200 mm**. Nowadays (**2007**) you would build you factory for **300 mm**.
- On this wafer we place our **chips**, square or rectangular areas that contain the complete integrated circuit with dimensions of roughly **1 cm^2**.
- The picture below shows a **150 mm** wafer with (rather large **1st** generation) **16 Mbit DRAM** chips and gives an idea about the whole structure.
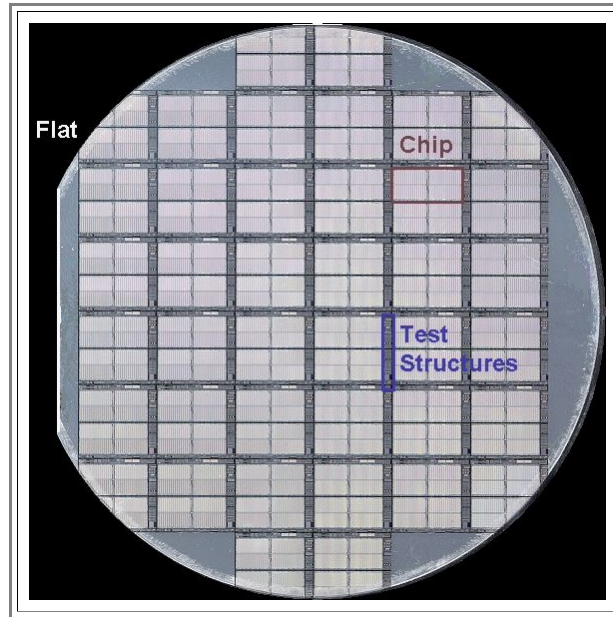
The chips will be cut with a diamond saw from the wafer and mounted in their casings.

- Between the chips - in the area that will be destroyed by cutting - are test structures that allow to measure certain technology parameters.
- 'The (major) **flat**" of the wafer is aligned along a **<110>** direction and allows to produce the structures on the wafer in perfect alignment with crystallographic directions. It also served to indicate the crystallography and doping type of the wafer; consult the link for details
- Don't forget: **Si** is *brittle like glass*. Handling a wafer is like handling a thin glass plate - if you are not careful, it breaks.

How to get the chips on the wafer? In order to produce a **CMOS** structure as shown before, we essentially have to go back and forth between two two basic process modules:

Material module

- Deposit some material on the surface of the wafer (e.g. **SiO$_2$**), or
- Modify material already there (e.g. by introducing the desired doping), or
- Clean the material present, or
- Measure something relative to the material (e.g. its thickness), or
- - well, there are a few more points like this but which are not important at this stage.

Structuring module

- Transfer the desired structure for the relevant material into some light sensitive layer called a photo-resist or simply **resist** (which is a very special *electronic material*!) by **lithography**, i.e. by projecting a slide (called a **mask** or more generally **reticle**) of the structure onto the light sensitive layer, followed by developing the resist akin to a conventional photographic process, and then:
- Transfer the structure from the resist to the material by **structure etching** or other techniques.

Repeat the cycle *more than 20 times* - and you have a wafer with fully processed chips.

- This is shown schematically in the drawing:
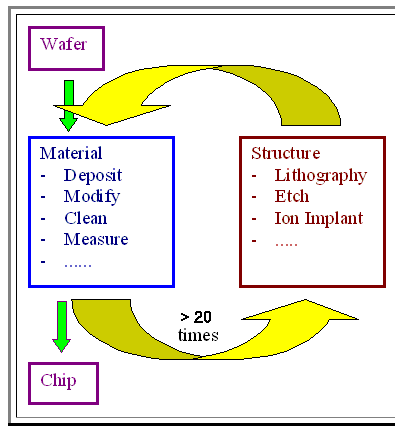
- For the most primitive transistor imaginable, a minimum of **5** lithographic steps are required. Each process module consists of many individual **process steps** and it is the art of **process integration** to find the optimal combination and sequence of process steps to achieve the desired result in the most economic way.

It needs a lot of process steps - most of them difficult and complex - to make a chip.

- Even the most simple **5** mask process requires about **100** process steps.
- A **16 Mbit DRAM** needs about **19** masks and **400** process steps.

To give an idea what this contains, here is a list of the ingredients for a **16 Mbit DRAM** at the time of its introduction to the market (with time it tends to become somewhat simpler):

- **57** layers are deposited (such as **SiO_2** (**14** times), **Si_3N_4**, **Al**, ...).
- **73** etching steps are necessary (**54** with "plasma etching", **19** with wet chemistry).
- **19** lithography steps are required (including deposition of the resist, exposure, and development).
- **12** high temperature processes (including several oxidations) are needed.
- **37** dedicated cleaning steps are built in; wet chemistry occurs **150** times altogether.
- **158** measurements take place to assure that everything happened as designed.

A more detailed rendering can be found in the link.

Two questions come to mind:

- *How long does it take to do all this?* The answer is: *weeks* if everything always works and you never have to wait, and *months* considering that there is no such thing as an uninterrupted process flow all the time.
- *How large is the success rate?* Well, lets do a back-of-the-envelope calculation and assume that each process has a success rate of **x %**. The overall **yield** **Y** of working devices is then
  $Y = (x/100)^N$ % with **N** = number of process steps. With **$N = 450$** or **200** we have

x	Y for $N = 450$	Y for $N = 200$
95%	$9{,}45 \cdot 10^{-9}$ %	$3{,}51 \cdot 10^{-3}$ %
99%	1,09 %	13,4 %
99,9%	63,7 %	81,9 %

- **N = 200** might be more realistic, because many steps (especially controls) do not influence the yield very much.

But whichever way we look at these numbers, there is an *unavoidable conclusion* : Total perfection at each process step is absolutely necessary!

Questionaire
Multiple Choice Questions to 5.2.1